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(71) Applicant: STEAG RTP SYSTEMS, INC. [US/US]; 4425 Fortran Drive, San Jose, CA 95134-2300 (US).

(72) Inventors: TAY, Sing, Pin; 45970 Tissiack Place, Fremont, CA 94539 (US). HU, Yao, Zhi; 2576 Lady Palm Court, San Jose, CA 95133 (US). SHARANGPANI, Rahul; 40640 High Street 103, Fremont, CA 94538 (US).

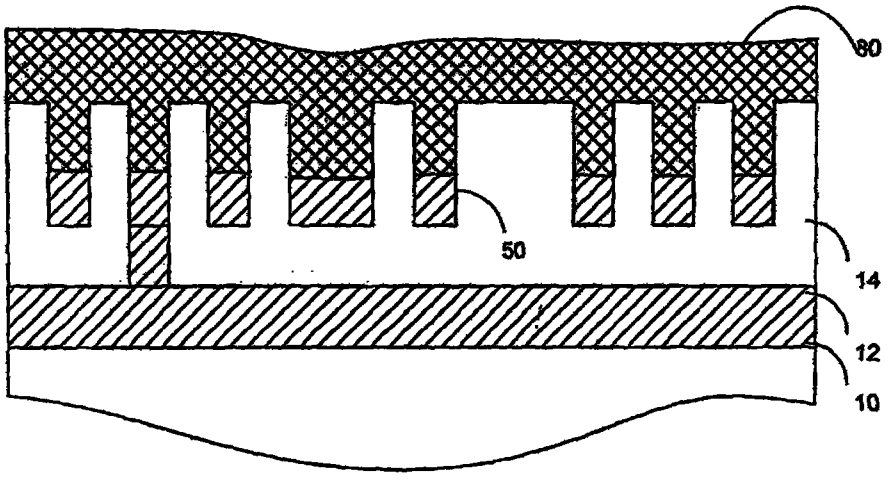
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(54) Title: METHOD OF PRODUCING COPPER FEATURES ON SEMICONDUCTOR WAFERS



(57) Abstract: Copper or a copper containing compound is deposited in holes or depressions in a substrate, and the copper material is oxidized to fill voids and defects in the copper material, and then reduced to produce a uniform filling of the depression by elemental copper.

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